



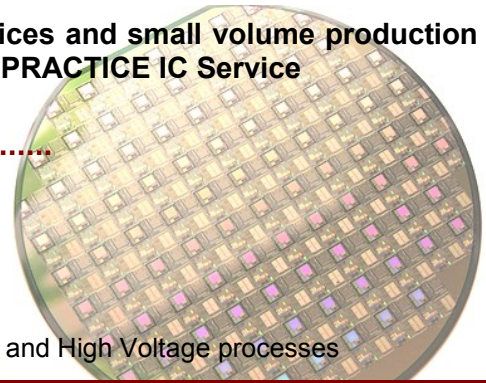
# EUROPRACTICE IC SERVICE

## ON Semi 0.7, 0.5, 0.35 & 0.18µ CMOS and HV

IMEC and On Semi agree to offer Multi Project Wafer Services and small volume production in CMOS and High Voltage technologies through the EUROPRACTICE IC Service

### Features and Benefits .....

- Cost reduction on prototypes
- Regular MPW runs
- Flexible access to silicon capacity for small volumes at OnSemi
- Deep Submicron RTL-to-Layout Service
- Available in 0.7µ, 0.5µ, 0.35µ, 0.18µ, CMOS Logic, Analog-Digital and High Voltage processes



0.7µ Logic A/D	0.7µ I2T100 100 V	0.5µ C05 F/N	0.35µ Logic A/D C035U	0.35µ I3T25 25 V	0.35µ I3T50 50 V
2M - 3M Al 3.3 or 5V IO HR poly Poly/Diff capacitor	2M - 3M Al 3.3 or 5V IO 100 V DMOS HR poly Poly/Diff & poly/poly capacitor N-DMOS P-DMOS	2M - 3M Al 2.5/3.3/5 V HR poly Poly/Poly capacitor	N-epi on P 3M - 5M Al 3.3 V IO HR poly MIM capacitor Poly/Poly capacitor	N-epi on P 3M - 5M Al 25 V DMOS 3.3 V IO HR poly MIM capacitor N-DMOS P-DMOS	N-epi on P 3M - 5M Al 50 V DMOS 3.3 V IO HR poly MIM capacitor N-DMOS P-DMOS

0.35µ I3T80 80 V	ONC18 1.8V/3.3V	ONC18 1.8V/5V	I4T 1.8V/3.3V	ONC18 1.8V/5V/18V
N-epi on P 3M - 5M Al 80 V DMOS 3.3 V IO HR poly MIM capacitor N-DMOS P-DMOS	4 to 6 Metal layers 1.0 to 4.0 fF/µm2 MIM capacitor 5V tolerant I/Os 5V Zener Diodes Schottky Diodes Deep N-Well (Triple Well/ Noise Isolation) Thick top metal High VT (low-leakage) option Native VT option Thick top metal 5V gate and 18, 24, 30 Vds transistor option 1.8V core cells libraries 1.8 memories ESD cells OTP and EEPROM	4 to 6 Metal layers 1.0 to 4.0 fF/µm2 MIM capacitor 1.8V, 5V I/Os 5V and HV Zener Diodes (HV) Schottky Diodes Thick top metal High VT (low-leakage) option Native VT option 5V gate and 18, 24, 30 Vds transistor 1.8V core cells libraries 1.8 memories ESD cells OTP and EEPROM	4 to 6 Metal layers 1.0-4.0 fF/µm2 MIM capacitor 5V tolerant I/Os 5V Zener Diodes Schottky Diodes Deep N-Well (Triple Well/ Noise Isolation) Thick top metal High VT (low-leakage) option Native VT option 1.8V gate and 30, 45, 75 Vds DMOS transistor 1.8V and 3.3V core cells libraries 1.8 and 3.3V memories ESD cells DTI isolation OTP and EEPROM	4 to 6 Metal layers 1.0 to 4.0 fF/µm2 MIM 1.8V, 5V I/Os 5V and HV Zener Diodes (HV) Schottky Diodes Thick top metal High VT (low-leakage) option Native VT option 5V gate and 18, 24, 30 Vds transistor 18V gate and 18Vds transistors 1.8V core library cells 1.8 memories ESD cells OTP and EEPROM

MPW runs in 2019	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
ON Semi 0.7µ C07M-D 2M/1P & ON Semi 0.7µ C07M-A 2M/1P/PdiffC/HR	14		25			3		12		28		
ON Semi 0.7µ C07M-I2T100 100 V - 2M & 3M options	14		25			3		12		28		
ON Semi 0.5µ CMOS EEPROM C5F & C5N - 200 mm			4*									
ON Semi 0.35µ C035U - 4M (3M & 5M optional) only thick top metal	28			15			1		16			2
ON Semi 0.35µ C035 - I3T25U 3.3/25 V 4M (3M & 5M optional) only thick top metal	28			15			1		16			2
ON Semi 0.35µ C035 - I3T80U 80 V 4M - 3M optional (5M on special request)	2			1			8			7		
ON Semi 0.35µ C035 - I3T50U (E) 50 V 4M - 3M optional (5M on special request)			4		27				2			2
ONC18MS (0.18 µm - 1.8/3.3 V - 15V DMOS - 5LM - MiMC - ESD - HiR - EPI)		4		8		10		12		7		9
ONC18MS-LL (=ONC18MS + High Vt)		4		8		10		12		7		9
ONC18HPA (= ONC18MS + DNW + Zener + Stacked MiMC + Native Dev + Schottky)		4		8		10		12		7		9
ONC18-I4T 45/70V HV CMOS (=ONC18MS + 30V + 45V + 70V DMOS)		4		8		10		12		7		9

All documentation & design kits available on : [www.europpractice-ic.com](http://www.europpractice-ic.com)

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